64 kb CMOS Parallel **EEPROM**

Description

The CAT28LV64 is a low voltage, low power, CMOS Parallel EEPROM organized as 8K x 8-bits. It requires a simple interface for in-system programming. On-chip address and data latches, self-timed write cycle with auto-clear and V_{CC} power up/down write protection eliminate additional timing and protection hardware. DATA Polling and Toggle status bit signal the start and end of the self-timed write cycle. Additionally, the CAT28LV64 features hardware and software write protection.

The CAT28LV64 is manufactured using ON Semiconductor's advanced CMOS floating gate technology. It is designed to endure 100,000 program/erase cycles and has a data retention of 100 years. The device is available in JEDEC approved 28-pin DIP, 28-pin TSOP, 28-pin SOIC or 32-pin PLCC packages.

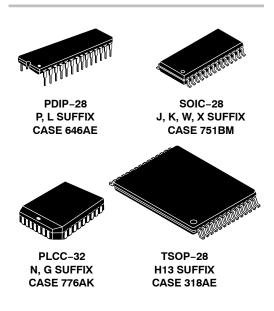
Features

- 3.0 V to 3.6 V Supply
- Read Access Times:
 - 150/200/250 ns
- Low Power CMOS Dissipation:
 - Active: 8 mA Max. - Standby: 100 μA Max.
- Simple Write Operation:
 - On-chip Address and Data Latches
 - Self-timed Write Cycle with Auto-clear
- Fast Write Cycle Time:
 - 5 ms Max.
- Commercial, Industrial and Automotive Temperature Ranges
- CMOS and TTL Compatible I/O
- Automatic Page Write Operation:
 - -1 to 32 bytes in 5 ms
 - Page Load Timer
- End of Write Detection:
 - Toggle bit
 - DATA Polling
- Hardware and Software Write Protection
- 100,000 Program/Erase Cycles
- 100 Year Data Retention
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



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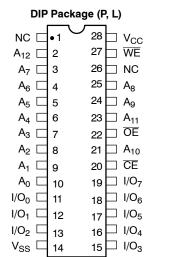
PIN FUNCTION

| Pin Name | Function | | |
|------------------------------------|-----------------------|--|--|
| A ₀ -A ₁₂ | Address Inputs | | |
| I/O ₀ -I/O ₇ | Data Inputs/Outputs | | |
| CE | Chip Enable | | |
| ŌĒ | Output Enable | | |
| WE | Write Enable | | |
| V _{CC} | 3.0 V to 3.6 V Supply | | |
| V _{SS} | Ground | | |
| NC | No Connect | | |

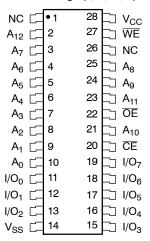
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 15 of this data sheet.

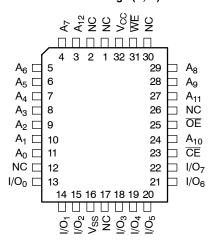
PIN CONFIGURATIONS



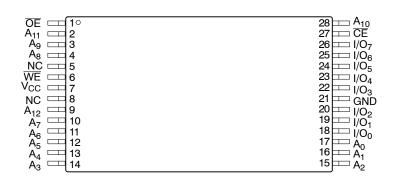
SOIC Package (J, K, W, X)



PLCC Package (N, G)



TSOP Package (8 mm x 13.4 mm) (H13)



(Top Views)

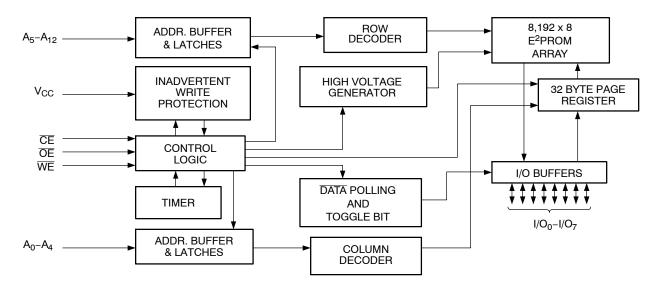


Figure 1. Block Diagram

Table 1. ABSOLUTE MAXIMUM RATINGS

| Parameters | Ratings | Units |
|--|------------------------------------|-------|
| Temperature Under Bias | -55 to +125 | °C |
| Storage Temperature | -65 to +150 | °C |
| Voltage on Any Pin with Respect to Ground (Note 1) | -2.0 V to +V _{CC} + 2.0 V | V |
| V _{CC} with Respect to Ground | -2.0 to +7.0 | V |
| Package Power Dissipation Capability (T _A = 25°C) | 1.0 | W |
| Lead Soldering Temperature (10 secs) | 300 | °C |
| Output Short Circuit Current (Note 2) | 100 | mA |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Table 2. RELIABILITY CHARACTERISTICS (Note 3)

| Symbol | Parameter | Test Method | Min | Max | Units |
|---------------------------|--------------------|-------------------------------|-----------------|-----|-------------|
| N _{END} | Endurance | MIL-STD-883, Test Method 1033 | 10 ⁵ | | Cycles/Byte |
| T _{DR} | Data Retention | MIL-STD-883, Test Method 1008 | 100 | | Years |
| V_{ZAP} | ESD Susceptibility | MIL-STD-883, Test Method 3015 | 2,000 | | V |
| I _{LTH} (Note 4) | Latch-Up | JEDEC Standard 17 | 100 | | mA |

^{3.} These parameters are tested initially and after a design or process change that affects the parameters.

Table 3. MODE SELECTION

| Mode | CE | WE | ŌĒ | I/O | Power |
|----------------------------|----|----|----|------------------|---------|
| Read | L | Н | L | D _{OUT} | ACTIVE |
| Byte Write (WE Controlled) | L | | Н | D _{IN} | ACTIVE |
| Byte Write (CE Controlled) | | L | Н | D _{IN} | ACTIVE |
| Standby and Write Inhibit | Н | Х | Х | High-Z | STANDBY |
| Read and Write Inhibit | Х | Н | Н | High-Z | ACTIVE |

^{1.} The minimum DC input voltage is -0.5 V. During transitions, inputs may undershoot to -2.0 V for periods of less than 20 ns. Maximum DC voltage on output pins is $V_{CC} + 0.5$ V, which may overshoot to $V_{CC} + 2.0$ V for periods of less than 20 ns.

^{2.} Output shorted for no more than one second. No more than one output shorted at a time.

^{4.} Latch-up protection is provided for stresses up to 100 mA on address and data pins from -1 V to V_{CC} + 1 V.

Table 4. CAPACITANCE ($T_A = 25$ °C, f = 1.0 MHz)

| Symbol | Test | Max | Conditions | Units |
|---------------------------|--------------------------|-----|-----------------|-------|
| C _{I/O} (Note 5) | Input/Output Capacitance | 10 | $V_{I/O} = 0 V$ | pF |
| C _{IN} (Note 5) | Input Capacitance | 6 | $V_{IN} = 0 V$ | pF |

^{5.} This parameter is tested initially and after a design or process change that affects the parameter.

Table 5. D.C. OPERATING CHARACTERISTICS ($V_{CC} = 3.0 \text{ V}$ to 3.6 V, unless otherwise specified.)

| | | | | Limits | | |
|---------------------------|--|--|------|--------|-----------------------|-------|
| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
| Icc | V _{CC} Current (Operating, TTL) | CE = OE = V _{IL} , f = 1/t _{RC} min, All I/O's Open | | | 8 | mA |
| I _{SBC} (Note 6) | V _{CC} Current (Standby, CMOS) | CE = V _{IHC} , All I/O's Open | | | 100 | μΑ |
| ILI | Input Leakage Current | V _{IN} = GND to V _{CC} | -1 | | 1 | μΑ |
| I _{LO} | Output Leakage Current | $\frac{V_{OUT}}{CE} = \text{GND to V}_{CC},$ | -5 | | 5 | μΑ |
| V _{IH} (Note 6) | High Level Input Voltage | | 2 | | V _{CC} + 0.3 | V |
| V _{IL} | Low Level Input Voltage | | -0.3 | | 0.6 | V |
| V _{OH} | High Level Output Voltage | I _{OH} = -100 μA | 2 | | | V |
| V _{OL} | Low Level Output Voltage | I _{OL} = 1.0 mA | | | 0.3 | V |
| V_{WI} | Write Inhibit Voltage | | 2 | | | V |

 $[\]overline{\text{6. V}_{IHC} = \text{V}_{CC}} - 0.3 \text{ V to V}_{CC} + 0.3 \text{ V}.$

Table 6. A.C. CHARACTERISTICS, READ CYCLE ($V_{CC} = 3.0 \text{ V}$ to 3.6 V, unless otherwise specified.)

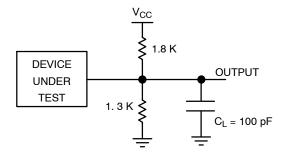
| | | 28LV64-15 | | 28LV6 | 64-20 | 28LV64-25 | | |
|-------------------------------|---------------------------------|-----------|-----|-------|-------|-----------|-----|-------|
| Symbol | Parameter | Min | Max | Min | Max | Min | Max | Units |
| t _{RC} | Read Cycle Time | 150 | | 200 | | 250 | | ns |
| t _{CE} | CE Access Time | | 150 | | 200 | | 250 | ns |
| t _{AA} | Address Access Time | | 150 | | 200 | | 250 | ns |
| t _{OE} | OE Access Time | | 70 | | 80 | | 100 | ns |
| t _{LZ} (Note 7) | CE Low to Active Output | 0 | | 0 | | 0 | | ns |
| t _{OLZ} (Note 7) | OE Low to Active Output | 0 | | 0 | | 0 | | ns |
| t _{HZ} (Notes 7, 8) | CE High to High-Z Output | | 50 | | 50 | | 55 | ns |
| t _{OHZ} (Notes 7, 8) | OE High to High-Z Output | | 50 | | 50 | | 55 | ns |
| t _{OH} (Note 7) | Output Hold from Address Change | 0 | | 0 | | 0 | | ns |

^{7.} This parameter is tested initially and after a design or process change that affects the parameter.
8. Output floating (High-Z) is defined as the state when the external data line is no longer driven by the output buffer.

 V_{CC} – 0.3 V – 2.0 V INPUT PULSE LEVELS REFERENCE POINTS 0.6 V 0.0 V -

Figure 2. A.C. Testing Input/Output Waveform (Note 9)

9. Input rise and fall times (10% and 90%) < 10 ns.



C_L INCLUDES JIG CAPACITANCE

Figure 3. A.C. Testing Load Circuit (example)

Table 7. A.C. CHARACTERISTICS, WRITE CYCLE (V_{CC} = 3.0 V to 3.6 V, unless otherwise specified.)

| | | 28LV | 64–15 | 28LV | 64–20 | 28LV | 64–25 | |
|------------------------------------|--|------|-------|------|-------|------|-------|-------|
| Symbol | Parameter | Min | Max | Min | Max | Min | Max | Units |
| t _{WC} | Write Cycle Time | | 5 | | 5 | | 5 | ms |
| t _{AS} | Address Setup Time | 0 | | 0 | | 0 | | ns |
| t _{AH} | Address Hold Time | 100 | | 100 | | 100 | | ns |
| t _{CS} | CE Setup Time | 0 | | 0 | | 0 | | ns |
| t _{CH} | CE Hold Time | 0 | | 0 | | 0 | | ns |
| t _{CW} (Note 10) | CE Pulse Time | 110 | | 150 | | 150 | | ns |
| t _{OES} | OE Setup Time | 0 | | 10 | | 10 | | ns |
| t _{OEH} | OE Hold Time | 0 | | 10 | | 10 | | ns |
| t _{WP} (Note 10) | WE Pulse Width | 110 | | 150 | | 150 | | ns |
| t _{DS} | Data Setup Time | 60 | | 100 | | 100 | | ns |
| t _{DH} | Data Hold Time | 0 | | 0 | | 0 | | ns |
| t _{INIT} (Note 11) | Write Inhibit Period After Power-up | 5 | 10 | 5 | 10 | 5 | 10 | ms |
| t _{BLC} (Notes 11, 12) | Byte Load Cycle Time | 0.05 | 100 | 0.1 | 100 | 0.1 | 100 | μs |

^{10.} A write pulse of less than 20 ns duration will not initiate a write cycle.11. This parameter is tested initially and after a design or process change that affects the parameter.

^{12.} A timer of duration t_{BLC} max. begins with every LOW to HIGH transition of WE. If allowed to time out, a page or byte write will begin; however a transition from HIGH to LOW within t_{BLC} max. stops the timer.

DEVICE OPERATION

Read

Data stored in the CAT28LV64 is transferred to the data bus when \overline{WE} is held high, and both \overline{OE} and \overline{CE} are held low. The data bus is set to a high impedance state when either \overline{CE} or \overline{OE} goes high. This 2–line control architecture can be used to eliminate bus contention in a system environment.

Byte Write

A write cycle is executed when both \overline{CE} and \overline{WE} are low, and \overline{OE} is high. Write cycles can be initiated using either \overline{WE} or \overline{CE} , with the address input being latched on the falling edge of \overline{WE} or \overline{CE} , whichever occurs last. Data, conversely, is latched on the rising edge of \overline{WE} or \overline{CE} , whichever occurs first. Once initiated, a byte write cycle automatically erases the addressed byte and the new data is written within 5 ms.

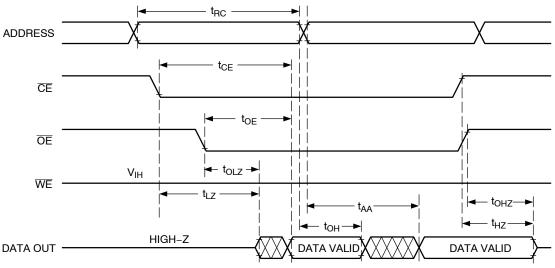


Figure 4. Read Cycle

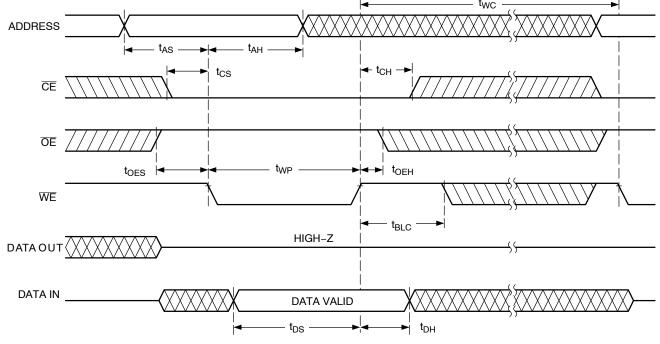


Figure 5. Byte Write Cycle [WE Controlled]

Page Write

The page write mode of the CAT28LV64 (essentially an extended BYTE WRITE mode) allows from 1 to 32 bytes of data to be programmed within a single EEPROM write cycle. This effectively reduces the byte–write time by a factor of 32.

Following an initial WRITE operation ($\overline{\text{WE}}$ pulsed low, for twp, and then high) the page write mode can begin by issuing sequential $\overline{\text{WE}}$ pulses, which load the address and data bytes into a 32 byte temporary buffer. The page address where data is to be written, specified by bits A_5 to A_{12} , is latched on the last falling edge of $\overline{\text{WE}}$. Each byte within the page is defined by address bits A_0 to A_4 (which can be loaded

in any order) during the first and subsequent write cycles. Each successive byte load cycle must begin within t_{BLCMAX} of the rising edge of the preceding \overline{WE} pulse. There is no page write window limitation as long as \overline{WE} is pulsed low within t_{BLCMAX} .

Upon completion of the page write sequence, \overline{WE} must stay high a minimum of $t_{BLC\,MAX}$ for the internal automatic program cycle to commence. This programming cycle consists of an erase cycle, which erases any data that existed in each addressed cell, and a write cycle, which writes new data back into the cell. A page write will only write data to the locations that were addressed and will not rewrite the entire page.

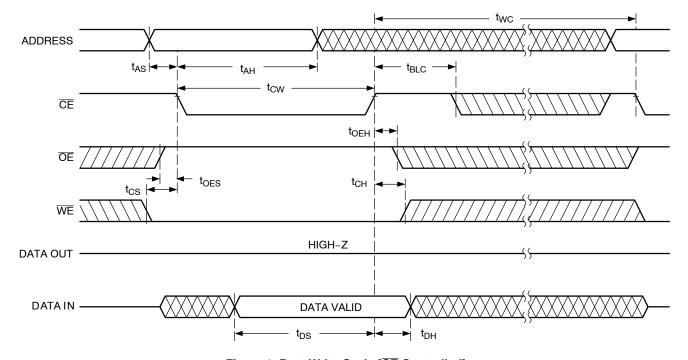


Figure 6. Byte Write Cycle [CE Controlled]

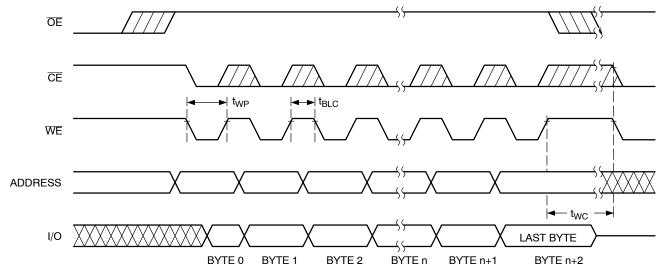


Figure 7. Page Mode Write Cycle

DATA Polling

 $\overline{\mathrm{DATA}}$ polling is provided to indicate the completion of write cycle. Once a byte write or page write cycle is initiated, attempting to read the last byte written will output the complement of that data on I/O₇ (I/O₀–I/O $_6$ are indeterminate) until the programming cycle is complete. Upon completion of the self–timed write cycle, all I/O's will output true data during a read cycle.

Toggle Bit

In addition to the \overline{DATA} Polling feature, the device offers an additional method for determining the completion of a write cycle. While a write cycle is in progress, reading data from the device will result in I/O₆ toggling between one and zero. However, once the write is complete, I/O₆ stops toggling and valid data can be read from the device.

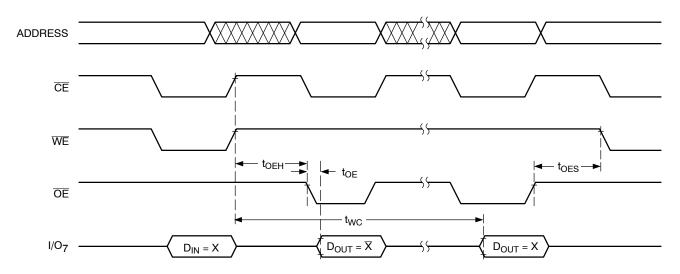


Figure 8. DATA Polling

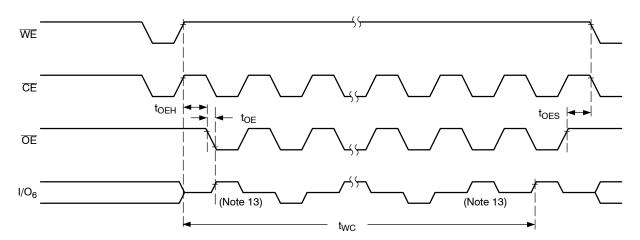


Figure 9. Toggle Bit

13. Beginning and ending state of I/O_6 is indeterminate.

Hardware Data Protection

The following is a list of hardware data protection features that are incorporated into the CAT28LV64.

- 1. V_{CC} sense provides for write protection when V_{CC} falls below 2.0 V min.
- A power on delay mechanism, t_{INIT} (see AC characteristics), provides a 5 to 10 ms delay before a write sequence, after V_{CC} has reached 2.40 V min.
- 3. Write inhibit is activated by holding any one of \overline{OE} low, \overline{CE} high or \overline{WE} high.

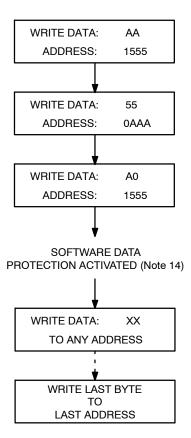


Figure 10. Write Sequence for Activating Software Data Protection

Noise pulses of less than 20 ns on the WE or CE inputs will not result in a write cycle.

Software Data Protection

The CAT28LV64 features a software controlled data protection scheme which, once enabled, requires a data algorithm to be issued to the device before a write can be performed. The device is shipped from ON Semiconductor with the software protection NOT ENABLED (the CAT28LV64 is in the standard operating mode).

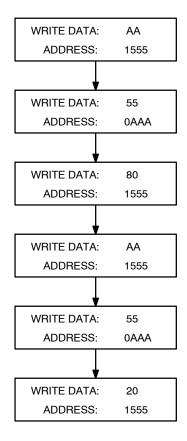


Figure 11. Write Sequence for Deactivating Software Data Protection

^{14.} Write protection is activated at this point whether or not any more writes are completed. Writing to addresses must occur within t_{BLC} Max., after SDP activation.

To activate the software data protection, the device must be sent three write commands to specific addresses with specific data (Figure 10). This sequence of commands (along with subsequent writes) must adhere to the page write timing specifications (Figure 12). Once this is done, all subsequent byte or page writes to the device must be preceded by this same set of write commands. The data protection mechanism is activated until a deactivate sequence is issued regardless of power on/off transitions. This gives the user added inadvertent write protection on power—up in addition to the hardware protection provided.

To allow the user the ability to program the device with an EEPROM programmer (or for testing purposes) there is a software command sequence for deactivating the data protection. The six step algorithm (Figure 11) will reset the internal protection circuitry, and the device will return to standard operating mode (Figure 13 provides reset timing). After the sixth byte of this reset sequence has been issued, standard byte or page writing can commence.

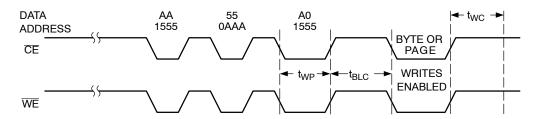


Figure 12. Software Data Protection Timing

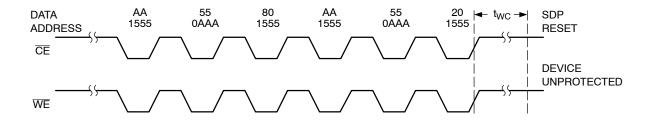
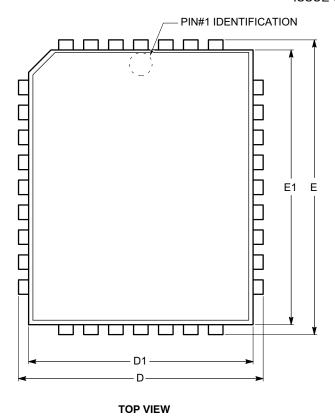
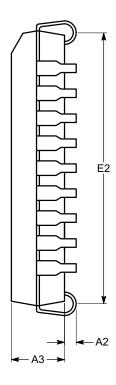


Figure 13. Resetting Software Data Protection Timing

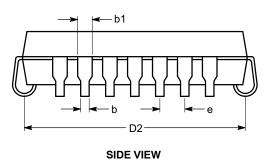
PACKAGE DIMENSIONS

PLCC 32 CASE 776AK-01 ISSUE O





END VIEW

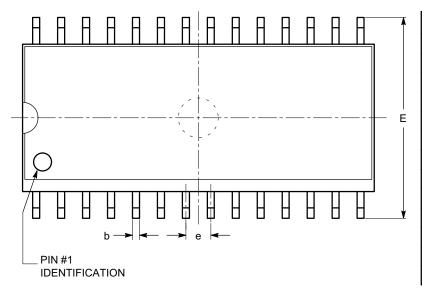


- (1) All dimensions are in millimeters.(2) Complies with JEDEC MS-016.

| SYMBOL | MIN | NOM | MAX |
|--------|-------|----------|-------|
| A2 | 0.38 | | |
| A3 | 2.54 | | 2.80 |
| b | 0.33 | | 0.54 |
| b1 | 0.66 | | 0.82 |
| D | 12.32 | | 12.57 |
| D1 | 11.36 | | 11.50 |
| D2 | 9.56 | | 11.32 |
| Е | 14.86 | | 15.11 |
| E1 | 13.90 | | 14.04 |
| E2 | 12.10 | | 13.86 |
| е | | 1.27 BSC | |

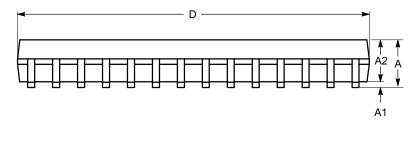
PACKAGE DIMENSIONS

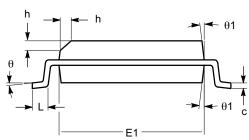
SOIC-28, 300 mils CASE 751BM-01 ISSUE O



| SYMBOL | MIN | NOM | MAX |
|--------|-------|----------|-------|
| А | 2.35 | | 2.65 |
| A1 | 0.10 | | 0.30 |
| A2 | 2.05 | | 2.55 |
| b | 0.31 | | 0.51 |
| С | 0.20 | | 0.33 |
| D | 17.78 | | 18.03 |
| Е | 10.11 | | 10.51 |
| E1 | 7.34 | | 7.60 |
| е | | 1.27 BSC | |
| h | 0.25 | | 0.75 |
| L | 0.40 | | 1.27 |
| θ | 0° | | 8° |
| θ1 | 5° | | 15° |

TOP VIEW





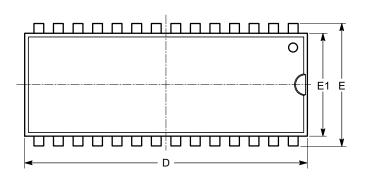
SIDE VIEW

END VIEW

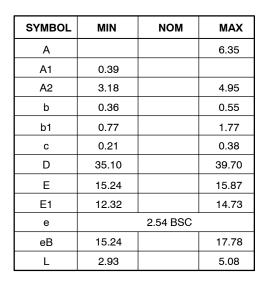
- (1) All dimensions are in millimeters. Angles in degrees.(2) Complies with JEDEC MS-013.

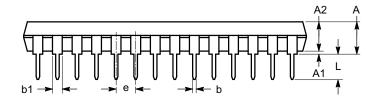
PACKAGE DIMENSIONS

PDIP-28, 600 mils CASE 646AE-01 ISSUE A



TOP VIEW



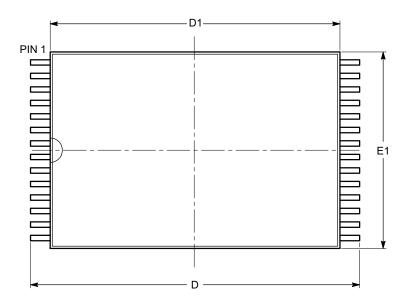


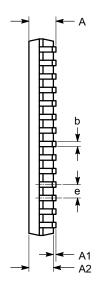


- (1) All dimensions are in millimeters.
- (2) Complies with JEDEC MS-011.

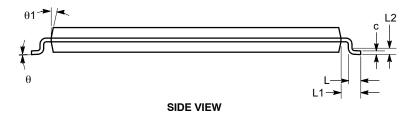
PACKAGE DIMENSIONS

TSOP 28, 8x13.4 CASE 318AE-01 ISSUE O





TOP VIEW

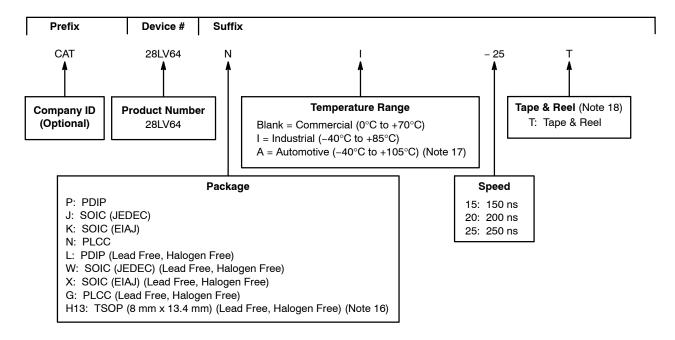


END VIEW

| SYMBOL | MIN | NOM | MAX | |
|--------|----------|----------|-------|--|
| Α | 1.00 | 1.10 | 1.20 | |
| A1 | 0.05 | | 0.15 | |
| A2 | 0.90 | 1.00 | 1.05 | |
| b | 0.17 | 0.22 | 0.27 | |
| С | 0.10 | 0.15 | 0.20 | |
| D | 13.20 | 13.40 | 13.60 | |
| D1 | 11.70 | 11.80 | 11.90 | |
| E | 7.90 | 8.00 | 8.10 | |
| е | | 0.55 BSC | | |
| L | 0.30 | 0.50 | 0.70 | |
| L1 | 0.675 | | | |
| L2 | 0.25 BSC | | | |
| θ | 0° | 3° | 5° | |
| θ1 | 10° | 12° | 16° | |

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MS-183.

Example of Ordering Information (Note 15)



ORDERING INFORMATION

| Orderable Part Numbers (for Pb-Free Devices) | | | | | |
|--|------------------|-----------------|-----------------|--|--|
| CAT28LV64GI-15T | CAT28LV64H13A15T | CAT28LV64WI-15T | CAT28LV64XA-15T | | |
| CAT28LV64GI-20T | CAT28LV64H13A20T | CAT28LV64WI-20T | CAT28LV64XA-20T | | |
| CAT28LV64GI-25T | CAT28LV64H13A25T | CAT28LV64WI-25T | CAT28LV64XA-25T | | |
| CAT28LV64GA-15T | CAT28LV64LI15 | CAT28LV64WA-15T | | | |
| CAT28LV64GA-20T | CAT28LV64LI20 | CAT28LV64WA-20T | | | |
| CAT28LV64GA-25T | CAT28LV64LI25 | CAT28LV64WA-25T | | | |
| CAT28LV64H13I15T | CAT28LV64LA15 | CAT28LV64XI-15T | | | |
| CAT28LV64H13I20T | CAT28LV64LA20 | CAT28LV64XI-20T | | | |
| CAT28LV64H13l25T | CAT28LV64LA25 | CAT28LV64XI-25T | | | |

- 15. The device used in the above example is a CAT28LV64NI-25T (PLCC, Industrial temperature, 250 ns Access Time, Tape & Reel).
- 16. For the TSOP package (H13), the orderable part number does not contain a hyphen, example: CAT28LV64H13I20T.
- 17. -40°C to +125°C is available upon request.
- 18. For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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